

# ● PRINTER RUSH ●

(PTO ASSISTANCE)

Application : <u>10/716366</u>	Examiner : <u>Smart</u>	GAU : <u>2813</u>
From : <u>CA</u>	Location : <u>(IDC) FMF FDC</u>	Date : <u>5/18/05</u>
Tracking # : <u>06079639</u>		Week Date : <u>2/21/05</u>

DOC CODE	DOC DATE	MISCELLANEOUS
<input type="checkbox"/> 1449		<input type="checkbox"/> Continuing Data
<input type="checkbox"/> IDS		<input type="checkbox"/> Foreign Priority
<input checked="" type="checkbox"/> CLM	<u>1/7/05</u>	<input type="checkbox"/> Document Legibility
<input type="checkbox"/> IIFW		<input type="checkbox"/> Fees
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<input type="checkbox"/> DRW		
<input type="checkbox"/> OATH		
<input type="checkbox"/> 312		
<input type="checkbox"/> SPEC		

[RUSH] MESSAGE: Claim 10 lacks final period

Please Review

Thaddeus  
CA

[XRUSH] RESPONSE: \_\_\_\_\_

JA

INITIALS: JE

NOTE: This form will be included as part of the official USPTO record, with the Response document coded as XRUSH.

REV 10/04

10. (Currently Amended) A method for making a transistor device by laser synthesis directly onto a monolithic substrate ~~of~~ essentially of a crystalline or polycrystalline wide-bandgap semiconductor compound, said method comprising, the steps of:

a. providing a monolithic wide-bandgap semiconductor compound substrate having a reverse side ~~and~~ of essentially n-type semiconductive carriers responsive to laser synthesis conversion;

b. converting a first section of said substrate to a p-type semiconductive carrier by laser synthesis;

c. converting a second section of said substrate to a p-type semiconductive carrier by laser synthesis spaced apart from said first p-type carrier section, to thereby form a separation therebetween;

d. inscribing on said substrate by laser synthesis a first conductor connected to said first p-type section and a second conductor connected to said second p-type section, to provide electrical connections to said first and second p-type sections, respectively;

e. inscribing on said reverse side of said substrate a third ~~said~~ p-type ~~section~~ sections on said substrate, and a ~~third~~ conductor, said ~~third~~ conductors providing means for connecting said device to other ~~and~~ external components, elements and circuits, and to thereby provide a p-n-p type semiconductor transistor.

11. (Original) A method for making a transistor device of claim 10, which includes the steps of placing said p-n-p transistor in a hermetically sealed chamber having a laser beam transmission window therein, and forming a first dielectric layer on a surface of said substrate disposed between said spaced apart p-type carrier sections and a second conductor layer on top of said dielectric layer by means of laser synthesis and various selected metallo-organic gases introduced into said chamber, and said laser